



**AO8810**

**Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor**

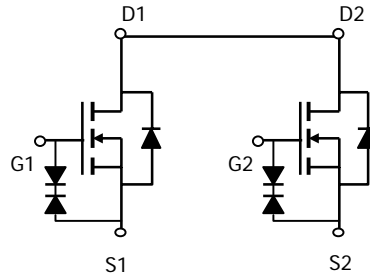
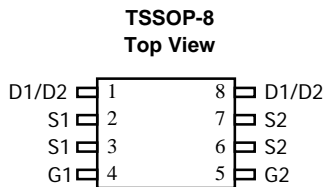


**General Description**

The AO8810 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. AO8810L is offered in a lead-free package. *Standard Product AO8810 is Pb-free (meets ROHS & Sony 259 specifications). AO8810L is a Green Product ordering option. AO8810 and AO8810L are electrically identical.*

**Features**

- $V_{DS}$  (V) = 20V
- $I_D$  = 7 A ( $V_{GS}$  = 4.5V)
- $R_{DS(ON)} < 20m\Omega$  ( $V_{GS}$  = 4.5V)
- $R_{DS(ON)} < 24m\Omega$  ( $V_{GS}$  = 2.5V)
- $R_{DS(ON)} < 32m\Omega$  ( $V_{GS}$  = 1.8V)
- ESD Rating: 2000V HBM



**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ\text{C}$	7	A
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	30	
Power Dissipation <sup>A</sup>	$T_A=25^\circ\text{C}$	1.5	W
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10\text{s}$	64	83	$^\circ\text{C/W}$
		Steady-State	89	120	$^\circ\text{C/W}$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	53	70	$^\circ\text{C/W}$	

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	20			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1	$\mu\text{A}$
					5	
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 4.5\text{V}$			$\pm 1$	$\mu\text{A}$
		$V_{DS}=0\text{V}$ , $V_{GS}=\pm 8\text{V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	0.4	0.6	1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$ , $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{V}$ , $I_D=7\text{A}$ $T_J=125^\circ\text{C}$		16.5	20	m $\Omega$
				23	28	
		$V_{GS}=2.5\text{V}$ , $I_D=5.5\text{A}$ $V_{GS}=1.8\text{V}$ , $I_D=5\text{A}$		20	24	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=7\text{A}$		29		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.76	1	V
$I_S$	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=10\text{V}$ , $f=1\text{MHz}$		1160		pF
$C_{oss}$	Output Capacitance			187		pF
$C_{rss}$	Reverse Transfer Capacitance			146		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		1.5		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=4.5\text{V}$ , $V_{DS}=10\text{V}$ , $I_D=7\text{A}$		16		nC
$Q_{gs}$	Gate Source Charge			0.8		nC
$Q_{gd}$	Gate Drain Charge			3.8		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=5\text{V}$ , $V_{DS}=10\text{V}$ , $R_L=1.35\Omega$ , $R_{GEN}=3\Omega$		6.2		ns
$t_r$	Turn-On Rise Time			12.7		ns
$t_{D(off)}$	Turn-Off DelayTime			51.7		ns
$t_f$	Turn-Off Fall Time			16		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=7\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		17.7		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=7\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		6.7		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

Rev 3 : June 2005

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

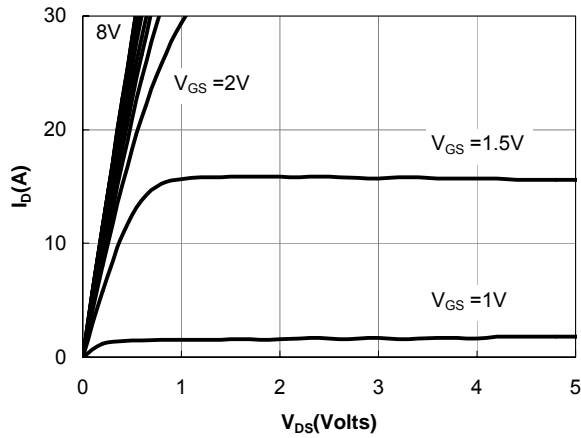


Figure 1: On-Regions Characteristic CS

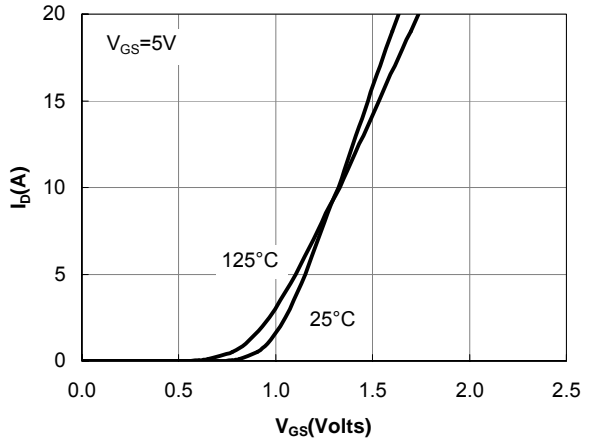


Figure 2: Transfer Characteristics

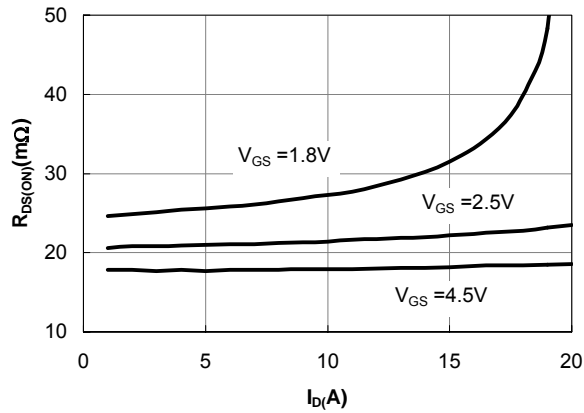


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

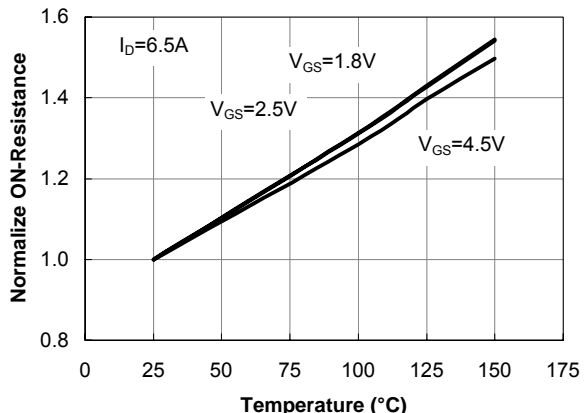


Figure 4: On-Resistance vs. Junction Temperature

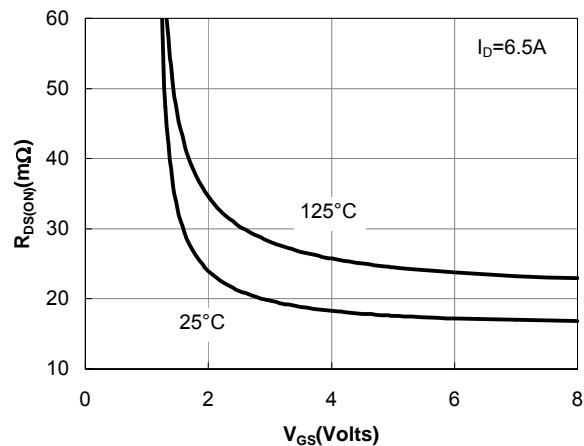


Figure 5: On-Resistance vs. Gate-Source Voltage

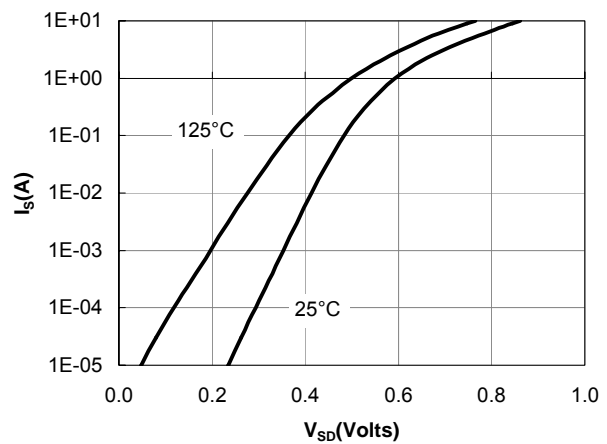


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

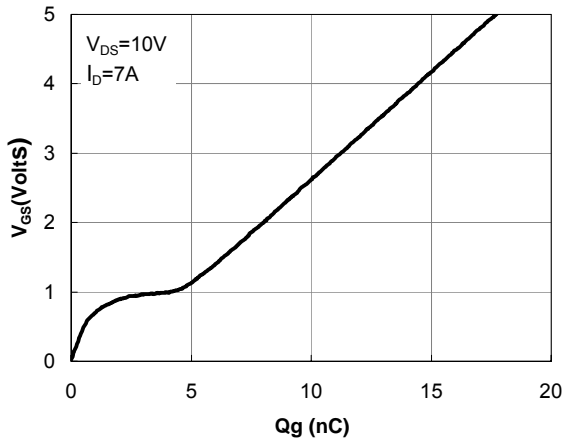


Figure 7: Gate-Charge Characteristics

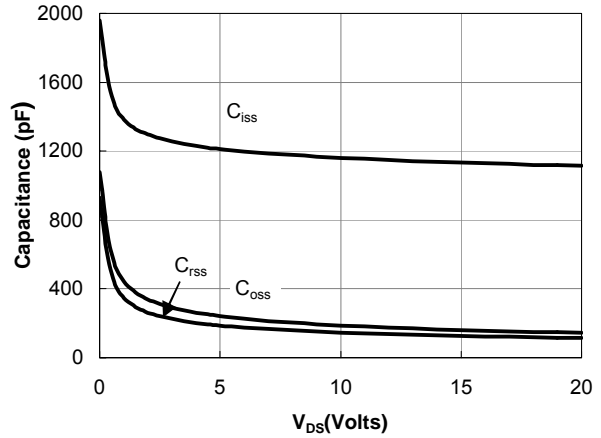


Figure 8: Capacitance Characteristics

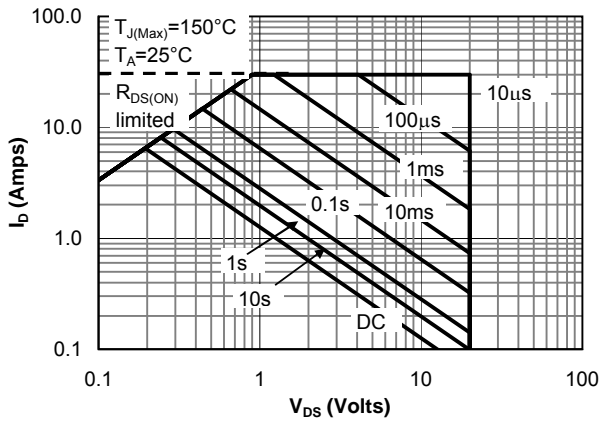


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

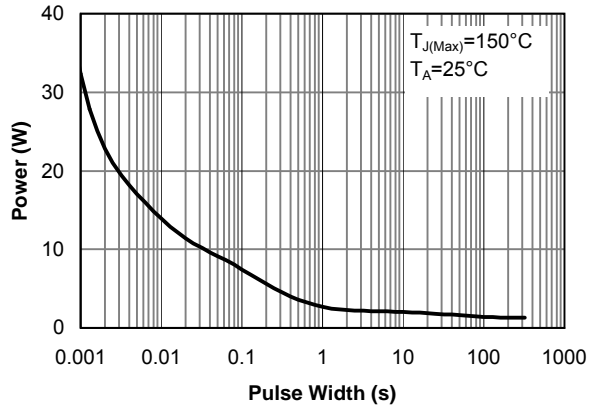


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

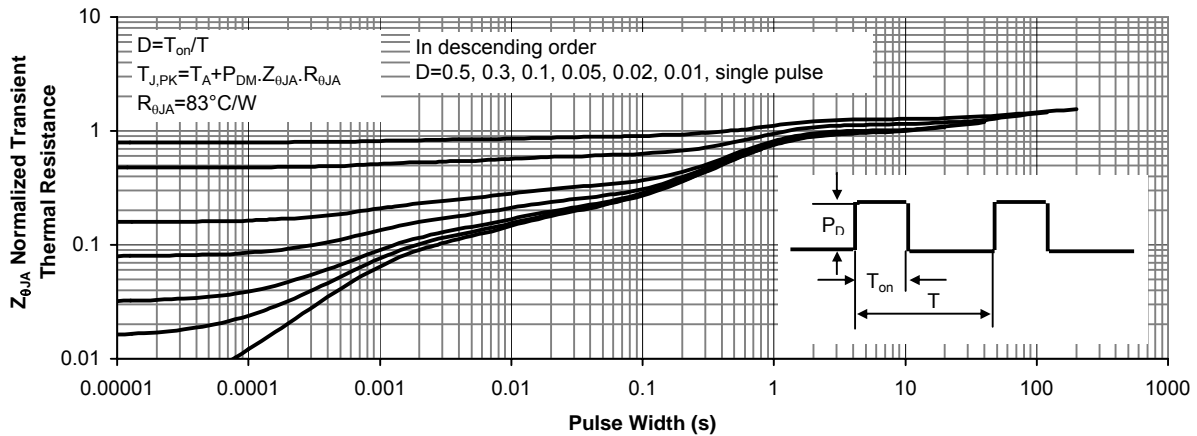


Figure 11: Normalized Maximum Transient Thermal Impedance